

**Silicon PNP Power Transistor**

**BD944F/946F/948F**

**DESCRIPTION**

- DC Current Gain-  
 $h_{FE} = 85(\text{Min}) @ I_C = -500\text{mA}$
- Complement to Type BD943F/945F/947F

**APPLICATIONS**

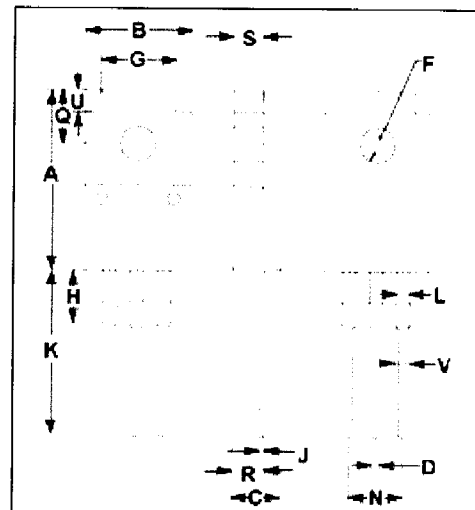
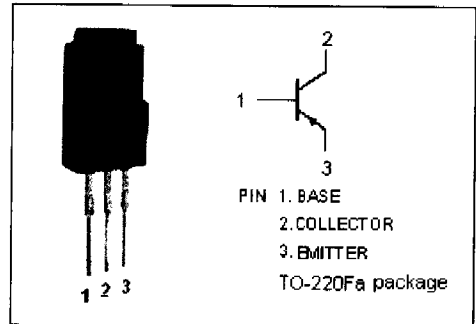
- Designed for use in audio output stages and general purpose amplifier applications.

**ABSOLUTE MAXIMUM RATINGS ( $T_a = 25^\circ\text{C}$ )**

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	BD944F	-22
		BD946F	-32
		BD948F	-45
$V_{CEO}$	Collector-Emitter Voltage	BD944F	-22
		BD946F	-32
		BD948F	-45
$V_{EBO}$	Emitter-Base Voltage	-5	V
$I_C$	Collector Current-Continuous	-5	A
$I_{CM}$	Collector Current-Peak	-8	A
$I_B$	Base Current-Continuous	-1	A
$P_C$	Collector Power Dissipation @ $T_C = 25^\circ\text{C}$	22	W
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature Range	-65~150	$^\circ\text{C}$

**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	7.93	$^\circ\text{C/W}$



DIM	mm	
	MIN	MAX
A	16.85	17.15
B	9.90	10.10
C	4.35	4.65
D	0.75	0.80
F	3.20	3.40
G	6.90	7.10
H	5.45	5.45
J	0.45	0.75
K	13.35	13.65
L	1.10	1.30
N	4.98	5.18
Q	4.85	5.15
R	2.95	3.25
S	2.70	2.90
U	1.75	2.05
V	1.30	1.50

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# Silicon PNP Power Transistor

# BD944F/946F/948F

## ELECTRICAL CHARACTERISTICS

$T_C=25^\circ\text{C}$  unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	BD944F	$I_C = -100\text{mA}; I_B = 0$	-22			V
		BD946F		-32			
		BD948F		-45			
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	BD944F/946F	$I_C = -2\text{A}; I_B = -0.2\text{A}$			-0.5	V
		BD948F	$I_C = -3\text{A}; I_B = -0.3\text{A}$			-0.7	
$V_{BE(on)}$	Base-Emitter On Voltage	BD944F/946F	$I_C = -2\text{A}; V_{CE} = -1\text{V}$			-1.1	V
		BD948F	$I_C = -3\text{A}; V_{CE} = -1\text{V}$			-1.3	
$I_{CBO}$	Collector Cutoff Current		$V_{CB} = V_{CB0max}; I_E = 0$ $V_{CB} = V_{CB0max}; I_E = 0, T_J = 150^\circ\text{C}$			-0.05 -1	mA
$I_{CEO}$	Collector Cutoff Current	BD944F	$V_{CE} = -15\text{V}; I_B = 0$			-0.1	mA
		BD946F	$V_{CE} = -20\text{V}; I_B = 0$				
		BD948F	$V_{CE} = -25\text{V}; I_B = 0$				
$I_{EBO}$	Emitter Cutoff Current		$V_{EB} = -5\text{V}; I_C = 0$			-0.2	mA
$h_{FE-1}$	DC Current Gain		$I_C = -10\text{mA}; V_{CE} = -5\text{V}$	25			
$h_{FE-2}$	DC Current Gain		$I_C = -500\text{mA}; V_{CE} = -1\text{V}$	85		475	
$h_{FE-3}$	DC Current Gain	BD944F/946F	$I_C = -2\text{A}; V_{CE} = -1\text{V}$	50			
		BD948F		40			
$h_{FE-4}$	DC Current Gain—Only For BD948F		$I_C = -3\text{A}; V_{CE} = -1\text{V}$	30			
$f_T$	Current-Gain—Bandwidth Product		$I_C = -250\text{mA}; V_{CE} = -1\text{V}$	3			MHz